U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
M122-2378SERIAL NO.
10/630,427 withLIST OF ART CITED BY APPLICANT
(Use several sheets if necessary)APPLICANT
Wendell P. NobleFILING DATE
July 29, 2003GROUP
Unassigned 2813

U.S. PATENT DOCUMENTS

| *Examiner Initial | | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate |
|-------------------|----|-----------------|-------|---------|-------|----------|----------------------------|
| AL | AA | 5,830,797 | 11/98 | Cleaves | | | |
| | AB | | | | | | |
| | AC | | | | | | |
| | AD | | | | | | |
| | AE | | | | | | |
| | AF | | | | | | |
| | AG | | | | | | |
| | AH | | | | | | |
| | AI | | | | | | |
| | AJ | | | | | | |
| | AK | | | | | | |
| | AL | | | | | | |
| | AM | | | | | | |
| | AN | | | | | | |
| | AO | | | | | | |
| | AP | | | | | | |

FOREIGN PATENT DOCUMENTS

| | Document Number | Date | Country | Class | Subclass | Translation | |
|--|-----------------|------|---------|-------|----------|-------------|----|
| | | | | | | Yes | No |
| | AQ | | | | | | |
| | AR | | | | | | |
| | AS | | | | | | |

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)


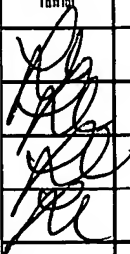
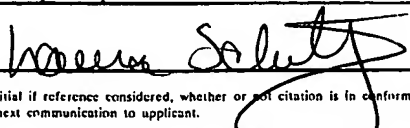
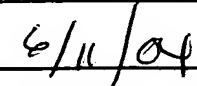
| | | | |
|--|----|--|--|
| | AT | | |
| | AU | | |

EXAMINER

DATE CONSIDERED

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EV317134631

|  | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | ATTY. DOCKET NO. M122-2378 | SERIAL NO. 10/630,427with | | | |
|--|----|---|-------|--|------------------------------|----------|----------------------------|----|
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| | | FILING DATE July 29, 2003 | | GROUP Unassigned 2813 | | | | |
| U.S. PATENT DOCUMENTS | | | | | | | | |
| *Examiner Initial | | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate | |
|  | AA | 5,604,159 | 02/97 | Conper, et al. | | | | |
| | AB | 6,277,708 | 08/01 | Bothra, et al. | | | | |
| | AC | 6,136,701 | 10/00 | Shin | | | | |
| | AD | 6,291,286 | 09/01 | Hsiao | | | | |
| | AE | | | | | | | |
| | AF | | | | | | | |
| | AG | | | | | | | |
| | AH | | | | | | | |
| | AI | | | | | | | |
| | AJ | | | | | | | |
| | AK | | | | | | | |
| | AL | | | | | | | |
| | AM | | | | | | | |
| | AN | | | | | | | |
| | AO | | | | | | | |
| | AP | | | | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | | |
| | | Document Number | Date | Country | Class | Subclass | Translation | |
| | | | | | | | Yes | No |
| | AQ | | | | | | | |
| | AR | | | | | | | |
| | AS | | | | | | | |
| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | | |
| | AT | | | | | | | |
| | AU | | | | | | | |
| EXAMINER | | | | DATE CONSIDERED | | | | |
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EV317154028

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| Form PTO-1449 | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | ATTY. DOCKET NO. M122-2378 | SERIAL NO. Filed Herewith |
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| | | | | FILING DATE Filed Herewith | GROUP <u>Unassigned</u> 2813 |

| U.S. PATENT DOCUMENTS | | | | | | | |
|-----------------------|-----------------|-----------|-------|--------------------|----------|----------------------------|--|
| *Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date if Appropriate | |
| AL | AA | 5,539,229 | 07/96 | Noble, Jr., et al. | | | |
| AL | AB | 5,214,603 | 05/93 | Dhong, et al. | | | |
| AL | AC | 4,604,162 | 08/86 | Sobczak | | | |
| AL | AD | 5,391,911 | 02/95 | Beyer, et al. | | | |
| AL | AE | 5,763,931 | 06/98 | Sugiyama | | | |
| AL | AF | 5,599,724 | 02/97 | Yoshida | | | |
| AL | AG | 5,846,854 | 12/98 | Giraud, et al. | | | |
| AL | AH | 5,011,783 | 04/91 | Ogawa, et al. | | | |
| AL | AI | 4,700,461 | 10/87 | Choi, et al. | | | |
| AL | AJ | 5,608,248 | 03/97 | Ohno | | | |
| AL | AK | 6,091,129 | 07/00 | Cleaves | | | |
| AL | AL | 6,004,865 | 12/99 | Horiuchi, et al. | | | |
| AL | AM | 5,831,305 | 11/98 | Kim | | | |
| AL | AN | 6,117,760 | 09/00 | Gardner, et al. | | | |
| AL | AO | 6,373,138 | 04/02 | Noble | | | |
| AL | AP | 6,274,919 | 08/01 | Wada | | | |

| FOREIGN PATENT DOCUMENTS | | | | | | | |
|--------------------------|--------------|---------|-------|----------|-------------|----|--|
| Document Number | Date | Country | Class | Subclass | Translation | | |
| | | | | | Yes | No | |
| AQ | 0 720 221 A1 | 07/96 | EPO | | | | |
| AR | | | | | | | |
| AS | | | | | | | |

| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | |
|---|----|--|
| AL | AT | Davari et al., "A Variable-Size Shallow Trench Isolation (STI) Technology With Diffused Sidewall Doping For Submicron CMOS," IEDM Technical Digest, International Electron Devices Meeting, San Francisco, CA, Dec. 11-14, 1988, pp. 92-95. |
| AL | AU | Bakeman et al., "A High Performance 16-Mb Dram Technology," 1990 Symposium on VLSI Technology Digest of Technical Papers, 1990 VLSI Technology Symposium, Honolulu, HI, June 4-7, 1990, pp. 11-12. |

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|-------------------------------------|----------------------------|
| EXAMINER <i>Wendell P. Noble</i> | DATE CONSIDERED 6/11/04 |
|-------------------------------------|----------------------------|

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EV317134177

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|--|--------------------|--|---------|---------|-------------------------------|-------------------------------|-------------------------------------|--|
| Form PTO-1449 | | U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE | | | ATTY. DOCKET NO. M122-2378 | | SERIAL NO. Filed Herewith | |
| LIST OF ART CITED BY APPLICANT <small>(Use several sheets if necessary)</small> | | | | | APPLICANT Wendell P. Noble | | | |
| | | | | | FILING DATE Filed Herewith | | GROUP Unassigned 2813 | |
| U.S. PATENT DOCUMENTS | | | | | | | | |
| *Examiner Initial | Document Number | Date | Name | Class | Subclass | Filing Date If Appropriate | | |
| | AA | 5,241,211 | 08/93 | Toshiro | | | | |
| | AB | | | | | | | |
| | AC | | | | | | | |
| FOREIGN PATENT DOCUMENTS | | | | | | | | |
| | Document Number | Date | Country | Class | Subclass | Translation | | |
| | | | | | | Yes | No | |
| | AP | | | | | | | |
| OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | | |
| | AS | Suma et al., "An SOI-DRAM With Wide Operating Voltage Range by CMOS/SIMOX Technology," <i>IEEE Journal of Solid-State Circuits</i> , November 1994, pp. 1323-1329. | | | | | | |
| | | Kuge et al., "SOI-DRAM Circuit Technologies For Low Power High Speed Multigiga Scale Memories", <i>IEEE Journal of Solid-State Circuits</i> , April 1996, pp. 586-591. | | | | | | |
| | | Y. Kohyama et al., "Buried Bit Line Cell for 64MB DRAMs," <i>IEEE, 1990 Symposium on VLSI Technology</i> , pp. 17, 18. | | | | | | |
| | | IBM Technical Disclosure Bulletin, "Buried Stud That Eliminates Substrate and Well Contact Requirements", Vol. 39, Pub No. 6, June 1996. | | | | | | |
| | | Takahiro Onai et al., "SEPIA: A New Isolation Structure for Soft-Error-Immune LSI's," 1993 <i>IEEE</i> , 3 pages. | | | | | | |
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